Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

Claims 1-9. (Canceled)

Claim 10. (Currently Amended) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the first wiring line and the second wiring line extend in parallel with each other,

wherein a width of the first wiring line is smaller than a width of the second wiring line, and the first and second wiring lines are arranged such that the second wiring line extends beyond opposite edges of the first wiring line, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 11. (Previously Presented) An integrated circuit using a thin film transistor according to claim 10, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 12. (Previously Presented) An integrated circuit using a thin film transistor according to claim 10, wherein the insulating film comprises silicon nitride.

Claim 13. (Previously Presented) An integrated circuit using a thin film transistor according to claim 10, wherein the insulating film comprises an interlayer insulating film.

Claim 14. (Previously Presented) An integrated circuit using a thin film transistor according to claim 10, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 15. (Previously Presented) An integrated circuit using a thin film transistor according to claim 10, wherein the second wiring comprises aluminum.

Claim 16. (Currently Amended) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion; **[[and]]**

an insulating film formed over the first wiring line;

a second wiring line formed over the first wiring line with the **[[an]]** insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line,

wherein the insulating film is interposed between the third wiring line and the first and second portions of the first wiring line, and between the third wiring line and the second wiring line,

wherein the first wiring line is formed on a same layer as a gate electrode of the thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 17. (Previously Presented) An integrated circuit using a thin film transistor according to claim 16, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 18. (Previously Presented) An integrated circuit using a thin film transistor according to claim 16, wherein the insulating film comprises silicon nitride.

Claim 19. (Previously Presented) An integrated circuit using a thin film transistor according to claim 16, wherein the insulating film comprises an interlayer insulating film.

Claim 20. (Previously Presented) An integrated circuit using a thin film transistor according to claim 16, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 21. (Previously Presented) An integrated circuit using a thin film transistor according to claim 16, wherein the second wiring comprises aluminum.

Claim 22. (Currently Amended) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion; **[[and]]**

an insulating film formed over the first wiring line;

a second wiring line formed over the first wiring line with the **[[an]]** insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line,

wherein the insulating film is interposed between the third wiring line and the first and second portions of the first wiring line, and between the third wiring line and the second wiring line,

wherein the second wiring line is formed on a same layer as a source or a drain electrode of the thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 23. (Previously Presented) An integrated circuit using a thin film transistor according to claim 22, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 24. (Previously Presented) An integrated circuit using a thin film transistor according to claim 22, wherein the insulating film comprises silicon nitride.

Claim 25. (Previously Presented) An integrated circuit using a thin film transistor according to claim 22, wherein the insulating film comprises an interlayer insulating film.

Claim 26. (Previously Presented) An integrated circuit using a thin film transistor according to claim 22, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 27. (Previously Presented) An integrated circuit using a thin film transistor according to claim 22, wherein the second wiring comprises aluminum.

Claim 28. (Currently Amended) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line,

wherein the first wiring line is formed on a same layer as a gate electrode of the thin film transistor,

wherein a width of the first wiring line is smaller than that of the second wiring line, and the first and second wiring lines are arranged such that the second wiring line extends beyond opposite edges of the first wiring line,

wherein the first wiring line and the second wiring line extend in parallel with each other, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 29. (Previously Presented) An integrated circuit using a thin film transistor according to claim 28, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 30. (Previously Presented) An integrated circuit using a thin film transistor according to claim 28, wherein the insulating film comprises silicon nitride.

Claim 31. (Previously Presented) An integrated circuit using a thin film transistor according to claim 28, wherein the insulating film comprises an interlayer insulating film.

Claim 32. (Previously Presented) An integrated circuit using a thin film transistor according to claim 28, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 33. (Previously Presented) An integrated circuit using a thin film transistor according to claim 28, wherein the second wiring comprises aluminum.

Claim 34. (Currently Amended) An integrated circuit using a thin film transistor comprising:

a first wiring line formed over a substrate; and

a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line,

wherein the second wiring is formed on a same layer as a source or a drain electrode of the thin film transistor,

wherein a width of the first wiring line is smaller than that of the second wiring line, and the first and second wiring lines are arranged such that the second wiring line extends beyond opposite edges of the first wiring line,

wherein the first wiring line and the second wiring line extend in parallel with each other, and

wherein the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

Claim 35. (Previously Presented) An integrated circuit using a thin film transistor according to claim 34, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

Claim 36. (Previously Presented) An integrated circuit using a thin film transistor according to claim 34, wherein the insulating film comprises silicon nitride.

Claim 37. (Previously Presented) An integrated circuit using a thin film transistor according to claim 34, wherein the insulating film comprises an interlayer insulating film.

Claim 38. (Previously Presented) An integrated circuit using a thin film transistor according to claim 34, wherein the first wiring comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

Claim 39. (Previously Presented) An integrated circuit using a thin film transistor according to claim 34, wherein the second wiring comprises aluminum.